

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	8	("20030030153" "5734200" "6251694" "6737745").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 12:48
L2	14577	copper with pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L3	137	L2 with window	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L4	68	L3 and wire	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L5	3458	copper with pad and barrier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L6	1269	L5 and barrier with pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L7	1269	L6 and barrier with pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L8	180	L6 and window	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L9	119	L8 and wire	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32

L10	118	L9 and (IC integrated adj circuit die wafer semiconductor silioecn chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L11	0	passivation with spin adj on adj process	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L12	57	passivation with spin near2 process	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L13	61	passivation with spin with pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L14	141	passivation with spin and pad with passivation and wire	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L15	103	L14 not L13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L16	740	advantages with spin near2 coat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L17	2	advantages with spin near2 coat\$3	USOCR	OR	ON	2006/01/21 13:32
L18	232	advantages with spin near2 coat\$3	USPAT	OR	ON	2006/01/21 13:32
L19	58	L18 and wire	USPAT	OR	ON	2006/01/21 13:32
L20	0	"20050208701".pn.	USPAT	OR	ON	2006/01/21 13:32
L21	1	"20050208701".pn.	US-PGPUB	OR	ON	2006/01/21 13:32
L22	5643	annealing with oxide indium with bismuth	US-PGPUB	OR	ON	2006/01/21 13:32
L23	3949	annealing with oxide indium near bismuth	US-PGPUB	OR	ON	2006/01/21 13:32
L24	0	annealing with oxide with indium near3 bismuth	US-PGPUB	OR	ON	2006/01/21 13:32

L25	1	annealing with oxide with indium near3 bismuth	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L26	1	anneal\$5 with oxide with indium near3 bismuth	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L27	9	anneal\$5 with oxide with(In adj bi)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L28	9	anneal\$5 with oxid\$3 with(In adj bi)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L29	0	oxid\$3 with(In adj bi)same protection with oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L30	5	oxid\$3 with(In adj bi)same protect\$3 with oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L31	2	"20030197258".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L32	0	("5685968.pn.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/21 13:32
L33	2	"5685968".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32

L34	1	L33 and defect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 13:32
L35	3917	(metallization pad contact wiring film layer) with (copper cu) and (overcoat coat passivation solder near2 resist patternable near2 material) and barrier and (window hole aperture opening)	US-PGPUB	OR	ON	2006/01/21 14:39
L36	137	((metallization pad contact wiring film layer) and (copper cu) and (overcoat coat passivation solder near2 resist patternable near2 material) and barrier and (window hole aperture opening)).clm.	US-PGPUB	OR	ON	2006/01/21 14:39
L37	137	((metallization pad contact wiring film layer) and (copper cu) and (overcoat coat passivation solder near2 resist patternable near2 material) and barrier and (window hole aperture opening)).clm.	US-PGPUB	OR	ON	2006/01/21 14:39